

LISTING OF THE CLAIMS

1-18 (Canceled).

19. (Previously Presented) An active matrix display device, comprising:

an insulation substrate;

a thin film transistor formed on the insulation substrate, including a semiconductor layer where source/drain regions are formed, gate electrode and source/drain electrodes respectively connected to the source/drain regions;

an insulation film formed over the insulation substrate, having an opening portion; and

a pixel electrode as a lower electrode,

wherein the source/drain electrodes have a dual-layered structure of a transparent conductive layer and a metal layer, the metal layer being enclosed by the insulation film,

wherein the pixel electrode extends from a portion of the transparent conductive layer forming any one of the source/drain electrodes and is exposed through the opening portion of the insulation film.

20. (Previously Presented) The active matrix display device according to claim 19, wherein the insulation film is a passivation layer patterned to cover the metal layer of the source/drain electrodes.

21. (Previously Presented) The active matrix display device according to claim 19, wherein the insulation film is a passivation layer reflowed to enclose the metal layer of the source/drain electrodes.

22. (Previously Presented) The active matrix display device according to claim 19, further comprising an organic EL layer formed on a portion of the pixel electrode exposed through the opening portion, wherein the organic EL layer is insulated from the metal layer of the source/drain electrodes.